

- GENERAL PURPOSE SILICON DIODES
- ALL JUNCTIONS COMPLETELY PROTECTED WITH SILICON DIOXIDE
- COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES EXCEPT SOLDER REFLOW

CD483B
 CD485B
 CD486B
 CD645
 AND
 CD5194 thru CD5196

MAXIMUM RATINGS

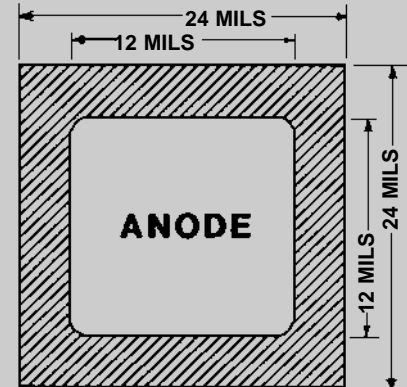
Operating Temperature: -65°C to +175°C
 Storage Temperature: -65°C to +175°C

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V _{RM}	V _{RWM}	I _O	I _O	I _{FSM}
	V(pk)	V(pk)	mA	T _A =+150°C	t _p = 1/120 S T _A =25°C
CD483B	80	70	200	50	2
CD485B	180	180	200	50	2
CD486B	250	225	200	50	2
CD645	270	225	400	150	5
CD5194	80	70	200	50	2
CD5195	180	180	200	50	2
CD5196	250	225	200	50	2

TYPE	V _F (1)	I _{R1} at V _{RWM}	I _{R2} at V _{RM}	I _{R3} at V _{RWM}	CAP
	V dc	nA dc	μA	μA dc	@V _R =4V
CD483B	0.8 - 1.0	25	100	5	-
CD485B	0.8 - 1.0	25	100	5	-
CD486B	0.8 - 1.0	25	100	5	-
CD645	0.8 - 1.0	50	50	25	2.0
CD5194	0.8 - 1.0	25	100	5	-
CD5195	0.8 - 1.0	25	100	5	-
CD5196	0.8 - 1.0	25	100	5	-

NOTE 1 AT 100mA (pulsed) except for CD645 which is at 400mA (pulsed)



DESIGN DATA

METALLIZATION:

Top: (Anode).....Al
 Back: (Cathode).....Au

AL THICKNESS25,000 Å Min

GOLD THICKNESS4,000 Å Min

CHIP THICKNESS10 Mils

TOLERANCES: ALL
 Dimensions ± 2 mils



CD483B, CD485B, CD486B, CD645, CD5194 thru CD5196

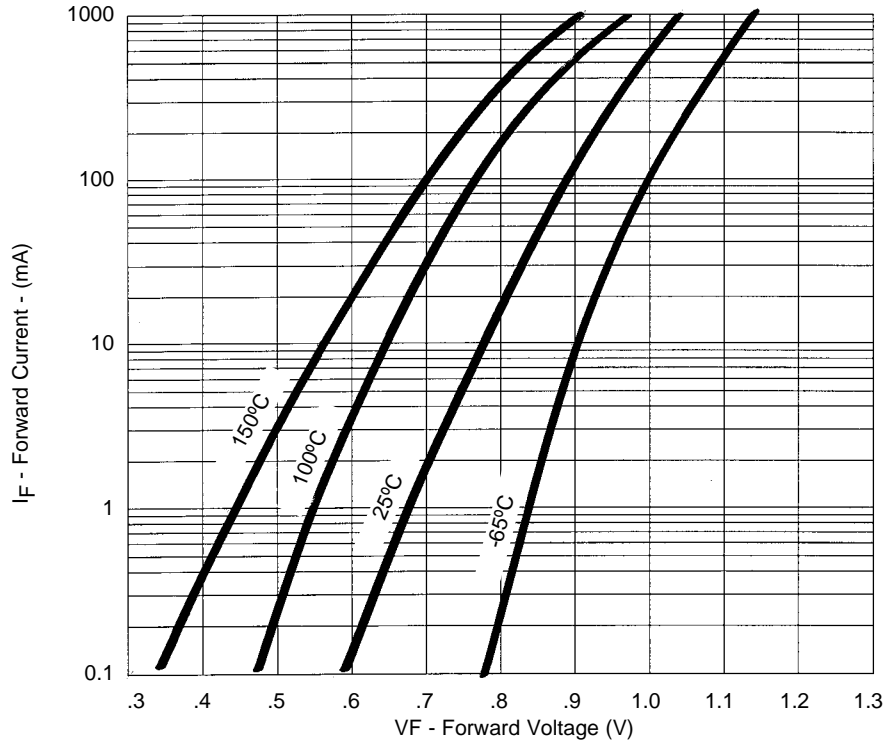
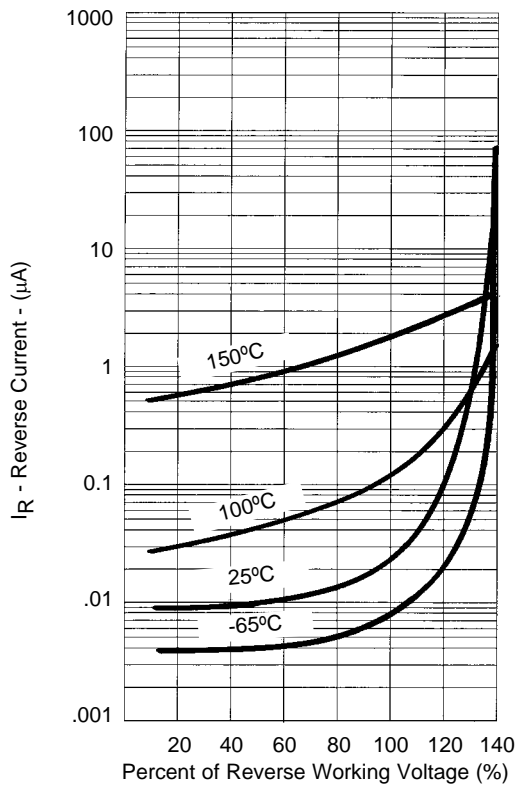


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage